Preferred Device

Amplifier Transistor

NPN Silicon

Features

• Pb-Free Package is Available

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Collector-Emitter Voltage	V _{CEO}	80	Vdc
Collector-Base Voltage	V _{CBO}	80	Vdc
Emitter-Base Voltage	V _{EBO}	6.0	Vdc
Collector Current – Continuous	Ic	500	mAdc

THERMAL CHARACTERISTICS

Characteristic	Symbol	Max	Unit	
Total Device Dissipation FR–5 Board (Note 1) T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C	
Thermal Resistance, Junction-to-Ambient (Note 1)	$R_{\theta JA}$	556	°C/W	
Total Device Dissipation Alumina Substrate (Note 2) T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C	
Thermal Resistance, Junction-to-Ambient (Note 2)	$R_{\theta JA}$	417	°C/W	
Junction and Storage Temperature Range	T _J , T _{stg}	-55 to +150	°C	

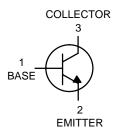
Maximum ratings are those values beyond which device damage can occur. Maximum ratings applied to the device are individual stress limit values (not normal operating conditions) and are not valid simultaneously. If these limits are exceeded, device functional operation is not implied, damage may occur and reliability may be affected.

- 1. $FR-5 = 1.0 \times 0.75 \times 0.062 \text{ in.}$
- 2. Alumina = 0.4 X 0.3 X 0.024 in. 99.5% alumina.



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SOT-23 (TO-236) CASE 318 STYLE 6

MARKING DIAGRAM



KB = Specific Device Code

M = Date Code* ■ Pb–Free Package

(Note: Microdot may be in either location)
*Date Code orientation and/or overbar may vary depending upon manufacturing location.

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBT8099LT1	SOT-23	3000/Tape & Reel
MMBT8099LT1G	SOT-23 (Pb-Free)	3000/Tape & Reel

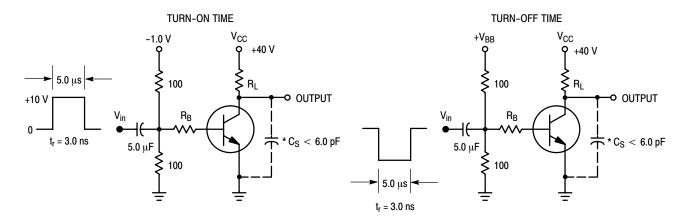
†For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

Preferred devices are recommended choices for future use and best overall value.

ELECTRICAL CHARACTERISTICS ($T_A = 25^{\circ}C$ unless otherwise noted)

Characteristic	Symbol	Min	Max	Unit		
OFF CHARACTERISTICS						
Collector – Emitter Breakdown Voltage (Note 3) (I _C = 10 mAdc, I _B = 0)	V _(BR) CEO	80	-	Vdc		
Collector – Base Breakdown Voltage $(I_C = 100 \mu Adc, I_E = 0)$	V _(BR) CBO	80	-	Vdc		
Emitter – Base Breakdown Voltage ($I_E = 10 \mu Adc, I_C = 0$)	V _{(BR)EBO}	6.0	-	Vdc		
Collector Cutoff Current $(V_{CE} = 60 \text{ Vdc}, I_B = 0)$	ICES	-	0.1	μAdc		
Collector Cutoff Current $(V_{CB} = 60 \text{ Vdc}, I_E = 0)$ $(V_{CB} = 80 \text{ Vdc}, I_E = 0)$	Ісво	_ _	0.1 -	μAdc		
Emitter Cutoff Current $(V_{EB} = 6.0 \text{ Vdc}, I_C = 0)$ $(V_{EB} = 4.0 \text{ Vdc}, I_C = 0)$	I _{EBO}	_ _	0.1 -	μAdc		
ON CHARACTERISTICS (Note 3)	·					
DC Current Gain	h _{FE}	100 100 75	300 - -	-		
Collector – Emitter Saturation Voltage ($I_C = 100 \text{ mAdc}$, $I_B = 5.0 \text{ mAdc}$) ($I_C = 100 \text{ mAdc}$, $I_B = 10 \text{ mAdc}$)	V _{CE(sat)}	_ _	0.4 0.3	Vdc		
Base–Emitter On Voltage ($I_C = 1.0 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$) ($I_C = 10 \text{ mAdc}$, $V_{CE} = 5.0 \text{ Vdc}$)	V _{BE(on)}	_ 0.6	_ 0.8	Vdc		
SMALL-SIGNAL CHARACTERISTICS	·	•				
Current – Gain – Bandwidth Product (I _C = 10 mAdc, V _{CE} = 5.0 Vdc, f = 100 MHz)	f⊤	150	_	MHz		
Output Capacitance (V _{CB} = 5.0 Vdc, I _E = 0, f = 1.0 MHz)	C _{obo}	_	6.0	pF		
Input Capacitance ($V_{EB} = 0.5 \text{ Vdc}$, $I_{C} = 0$, $f = 1.0 \text{ MHz}$)	C _{ibo}	_	25	pF		

^{3.} Pulse Test: Pulse Width \leq 300 μ s, Duty Cycle \leq 2.0%.



*Total Shunt Capacitance of Test Jig and Connectors For PNP Test Circuits, Reverse All Voltage Polarities

Figure 1. Switching Time Test Circuits

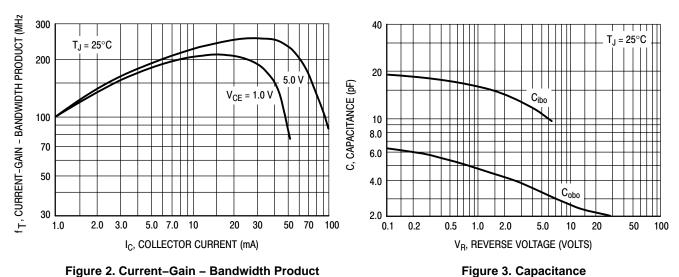


Figure 2. Current-Gain - Bandwidth Product

1.0 k

700

500

300

200

70

50

30

20

10

10

t, TIME (ns) 100 V_{CC} = 40 V

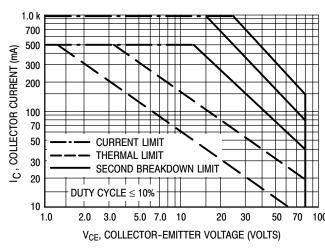
 $t_d @ V_{BE(off)} = 0.5 V$

20

30

 $I_C/I_B = 10$

 $I_{B1} = I_{B2}$ $T_J = 25^{\circ}C$



IC, COLLECTOR CURRENT (mA) Figure 4. Switching Times

50

70

100

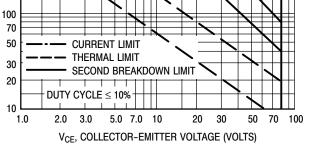


Figure 5. Active-Region Safe Operating Area

200

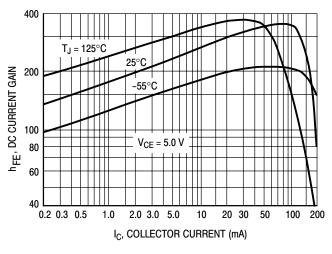


Figure 6. DC Current Gain

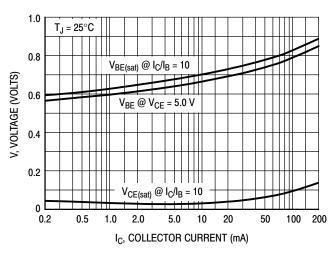


Figure 7. "ON" Voltages

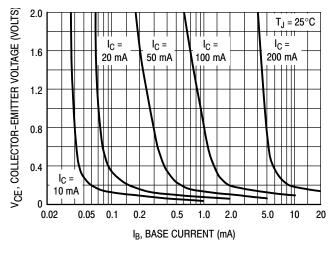


Figure 8. Collector Saturation Region

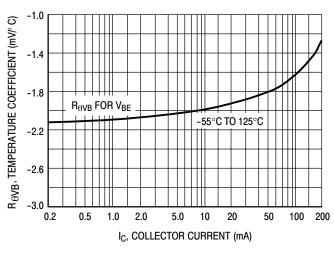


Figure 9. Base-Emitter Temperature Coefficient

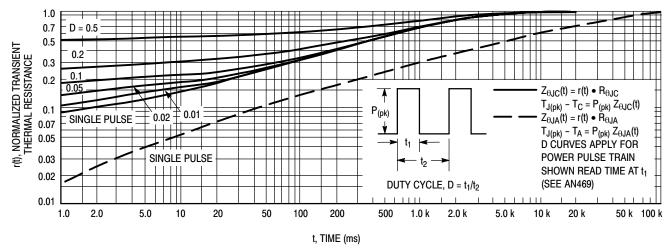
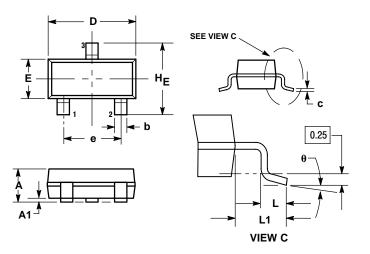


Figure 10. Thermal Response

PACKAGE DIMENSIONS

SOT-23 (TO-236) CASE 318-08 **ISSUE AN**



NOTES

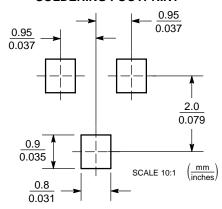
- DIMENSIONING AND TOLERANCING PER ANSI
- Y14.5M, 1982. CONTROLLING DIMENSION: INCH
- MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH THICKNESS. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF BASE MATERIAL.
- 318-01 THRU -07 AND -09 OBSOLETE, NEW STANDARD 318-08.

	MILLIMETERS			INCHES		
DIM	MIN	NOM	MAX	MIN	NOM	MAX
Α	0.89	1.00	1.11	0.035	0.040	0.044
A1	0.01	0.06	0.10	0.001	0.002	0.004
b	0.37	0.44	0.50	0.015	0.018	0.020
С	0.09	0.13	0.18	0.003	0.005	0.007
D	2.80	2.90	3.04	0.110	0.114	0.120
E	1.20	1.30	1.40	0.047	0.051	0.055
е	1.78	1.90	2.04	0.070	0.075	0.081
L	0.10	0.20	0.30	0.004	0.008	0.012
L1	0.35	0.54	0.69	0.014	0.021	0.029
ΗE	2.10	2.40	2.64	0.083	0.094	0.104

STYLE 6:

- PIN 1. BASE 2. EMITTER COLLECTOR

SOLDERING FOOTPRINT*



*For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

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